



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TC 2800 MAIL ROOM

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In re the Application of:

**Hitoshi ASADA et al.**

Serial Number: **09/753,616**

Group Art Unit: **2811**

Filed: **January 4, 2001**

Examiner: **Samuel A. GEBREMARIAM**

For: **CMOS IMAGE SENSOR AND MANUFACTURING METHOD OF THE SAME**

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner of Patents and Trademarks  
Washington, D.C. 20231

August 12, 2002

Sir:

In response to the Office Action dated April 12, 2002, please amend the above-identified application as follows:

**IN THE SPECIFICATION:**

Please amend the specification as follows:

**Please replace the paragraph beginning at page 9, line 27, with the following rewritten paragraph:**

A' Next, as shown in Fig. 4B and Fig. 12B, the entire surface of the resultant structure is coated with a photoresist film 13 so as to cover the silicon nitride film 11, and an opening portion is provided at a portion corresponding to a P channel MOS transistor formation portion after exposure and developing steps. Phosphorus (P) is ion-injected to the semiconductor substrate 10 through the opening portion under conditions of, for example, 180 keV and  $1.4 \times 10^{13}/\text{cm}^2$ , and